

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE (L²- π -MOS V)

2 S J 3 7 8

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

RELAY DRIVE, DC-DC CONVERTER AND MOTOR DRIVE

APPLICATIONS

- 4V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.16\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.0S$ (Typ.)
- Low Leakage Current : $I_{DSS} = -100\mu A$ (Max.) ($V_{DS} = -60V$)
- Enhancement-Mode : $V_{th} = -0.8 \sim -2.0V$
($V_{DS} = -10V$, $I_D = -1mA$)

MAXIMUM RATINGS (T_a = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	-60	V
Drain-Gate Voltage ($R_{GS}=20k\Omega$)		V_{DGR}	-60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	-5	A
	Pulse	I_{DP}	-20	A
Drain Power Dissipation ($T_a=25^{\circ}C$)		P_D	1.3	W
Single Pulse Avalanche Energy**		E_{AS}	273	mJ
Avalanche Current		I_{AR}	-5	A
Repetitive Avalanche Energy*		E_{AR}	0.13	mJ
Channel Temperature		T_{ch}	150	$^{\circ}C$
Storage Temperature Range		T_{stg}	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	96.1	°C/W

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

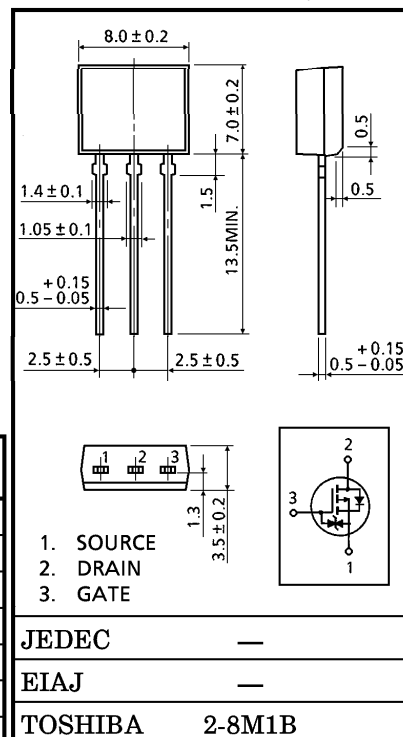
** $V_{DD} = -25V$, Starting $T_{ch} = 25^{\circ}C$, $L = 14.84mH$, $R_G = 25\Omega$, $I_{AB} = -5A$

This transistor is an electrostatic sensitive device.

Please handle with caution.

INDUSTRIAL APPLICATIONS

Unit in mm

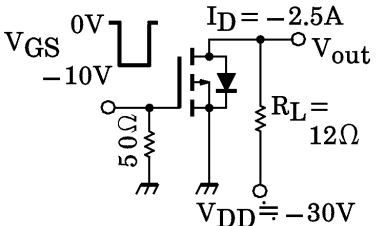


Weight : 0.54g

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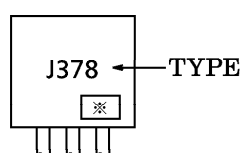
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	—	—	-100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = -10mA, V_{GS} = 0V$	-60	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = -10V, I_D = -1mA$	-0.8	—	-2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = -4V, I_D = -2.5A$	—	0.24	0.28	Ω
			$V_{GS} = -10V, I_D = -2.5A$	—	0.16	0.19	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = -10V, I_D = -2.5A$	2.0	4.0	—	S
Input Capacitance		C_{iss}	$V_{DS} = -10V, V_{GS} = 0V$ $f = 1MHz$	—	630	—	pF
Reverse Transfer Capacitance		C_{rss}		—	95	—	
Output Capacitance		C_{oss}		—	290	—	
Switching Time	Rise Time	t_r	 $V_{IN} : t_r, t_f < 5ns$ $Duty \leq 1\%, t_w = 10\mu s$	—	25	—	ns
	Turn-on Time	t_{on}		—	45	—	
	Fall Time	t_f		—	55	—	
	Turn-off Time	t_{off}		—	200	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} = -48V, V_{GS} = -10V$ $I_D = -5A$	—	22	—	nC
Gate-Source Charge		Q_{gs}		—	16	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	6	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	-5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	-20	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = -5A, V_{GS} = 0V$	—	—	1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = -5A, V_{GS} = 0V$	—	80	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 50A / \mu s$	—	0.1	—	μC

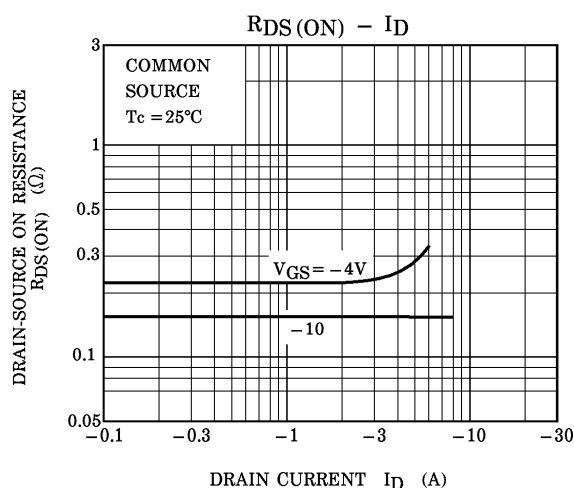
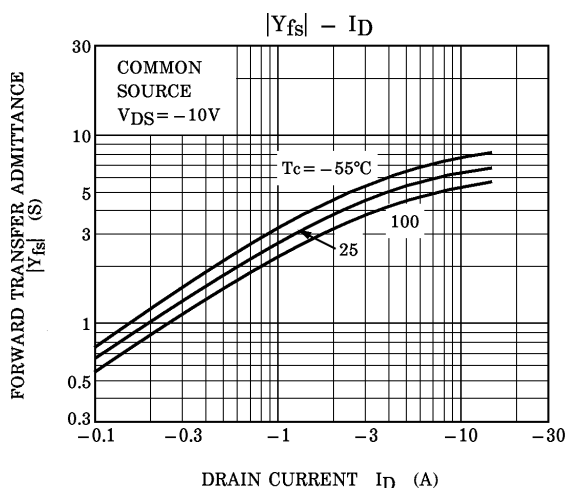
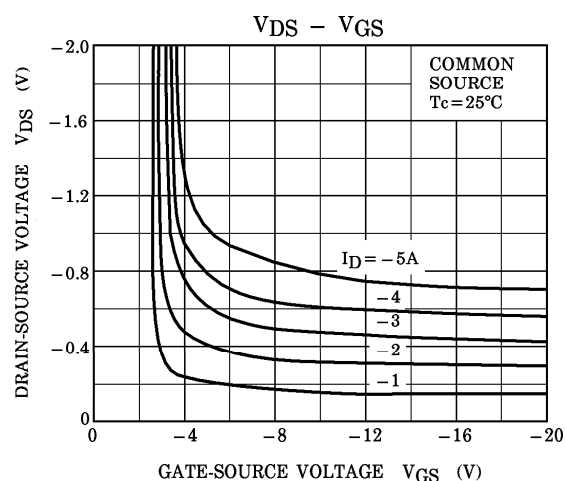
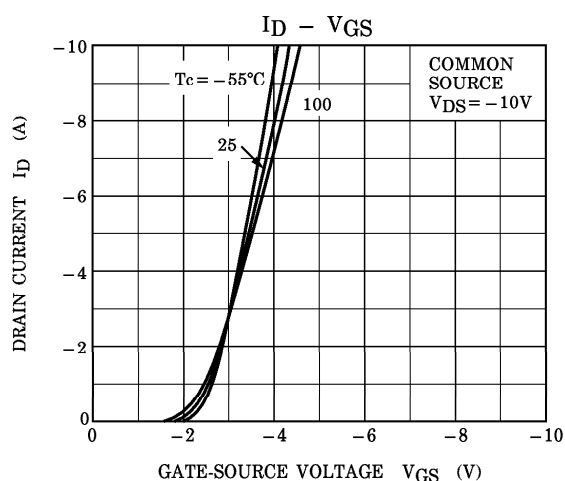
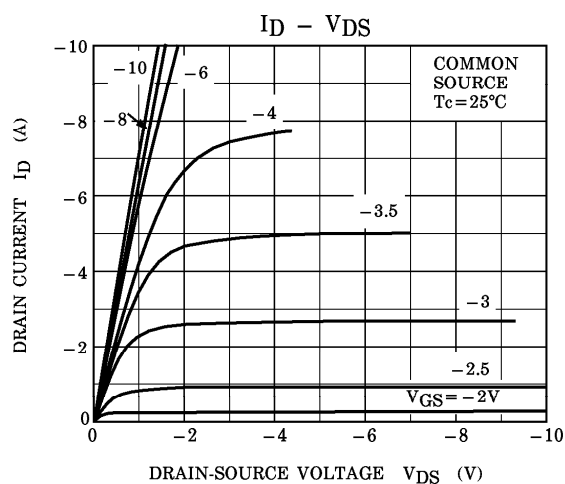
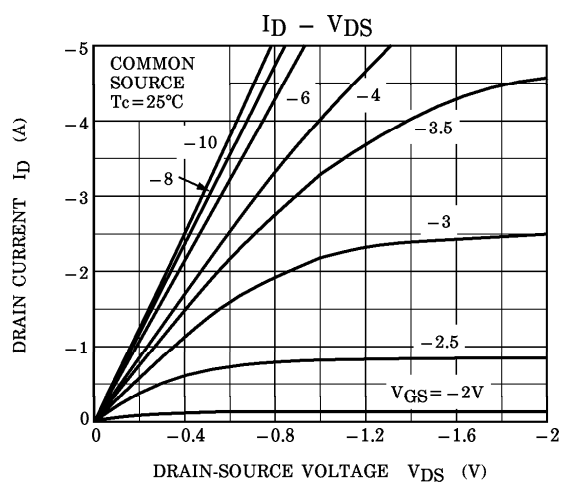
MARKING

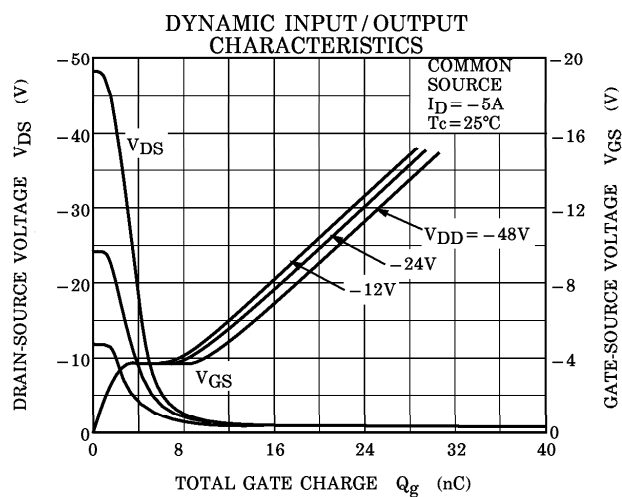
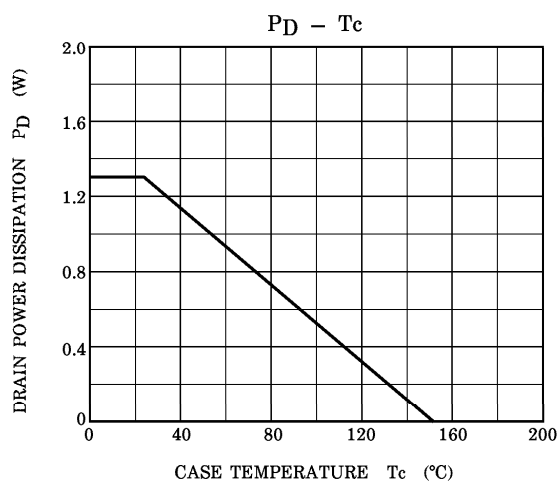
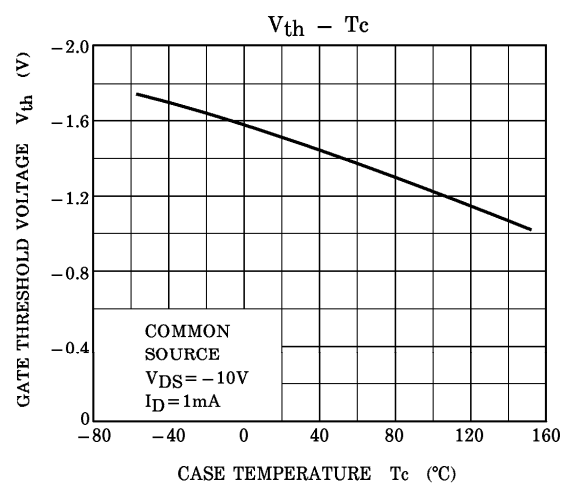
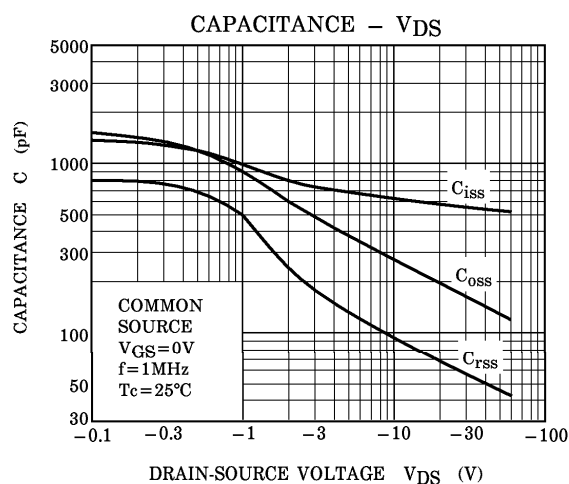
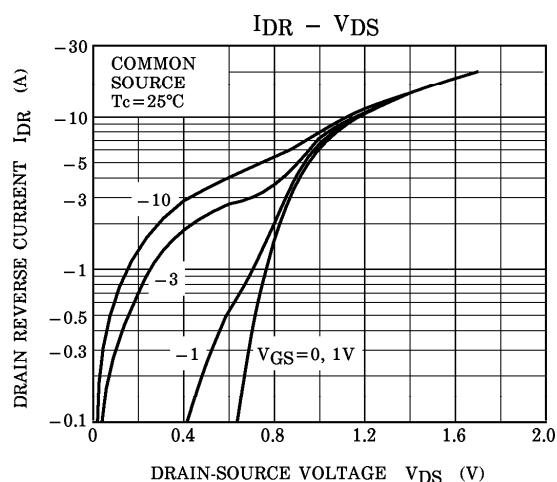
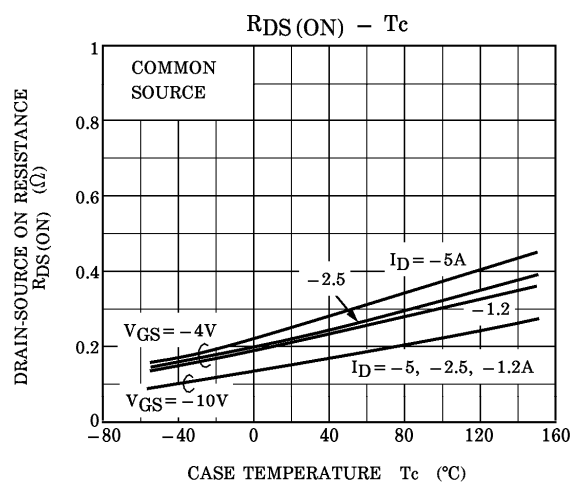


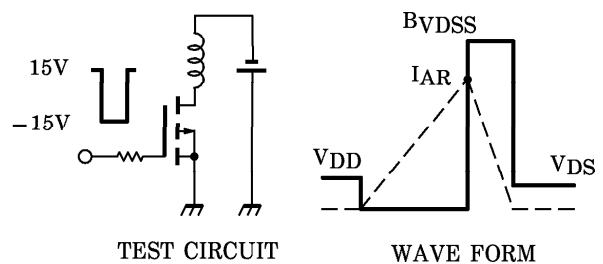
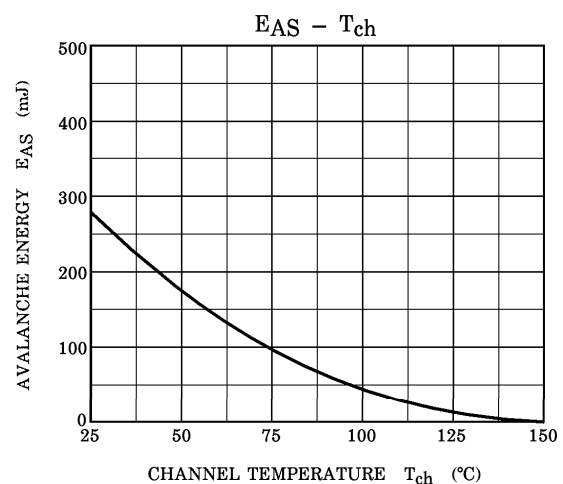
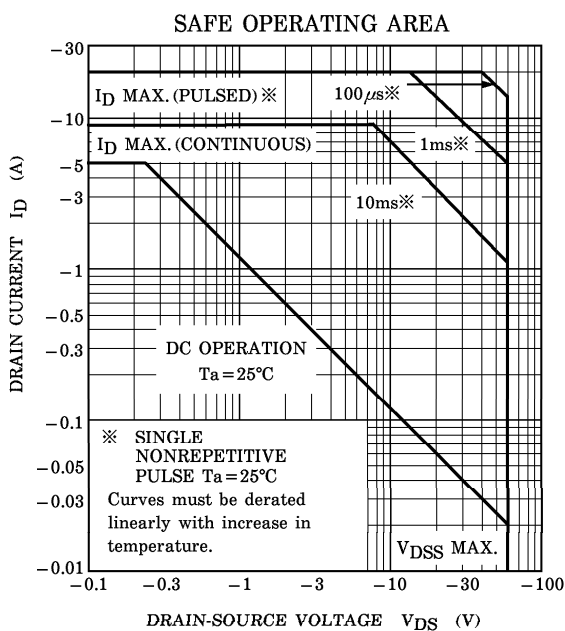
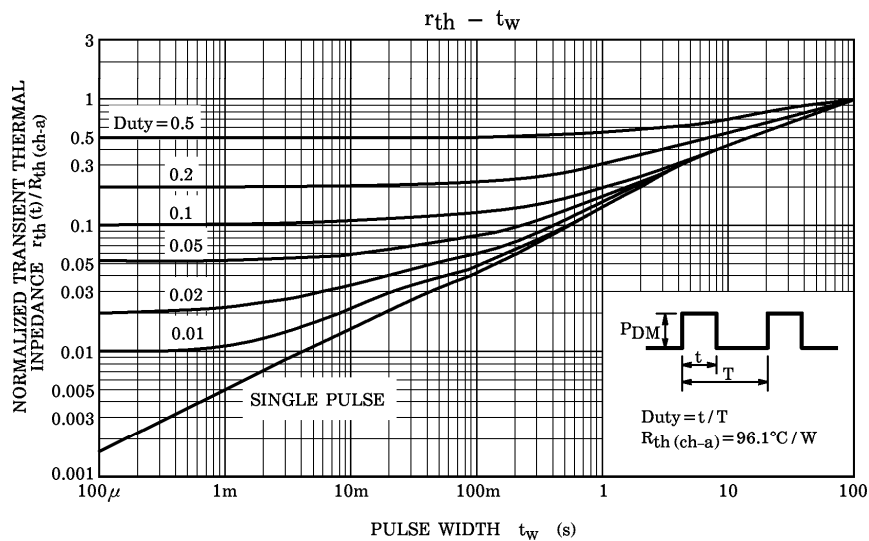
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







$\text{Peak } I_{AR} = -5A, R_G = 25\Omega$
 $V_{DD} = -25V, L = 14.84mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{V_{DS}}}{B_{V_{DS}} - V_{DD}} \right)$$